1. General description

The 74AUP1G11 provides a low-power, low-voltage single 3-input AND gate.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \ \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C





3. Ordering information

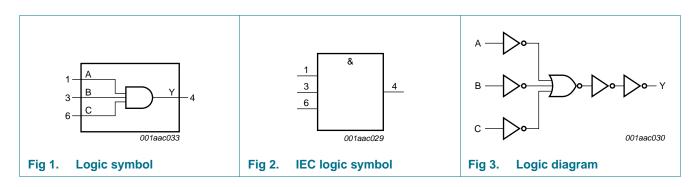
Table 1. Ordering information										
Type number Package										
	Temperature range	Name	Description	Version						
74AUP1G11GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363						
74AUP1G11GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886						
74AUP1G11GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891						
74AUP1G11GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115						
74AUP1G11GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202						

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP1G11GW	pU
74AUP1G11GM	pU
74AUP1G11GF	pU
74AUP1G11GN	pU
74AUP1G11GS	pU

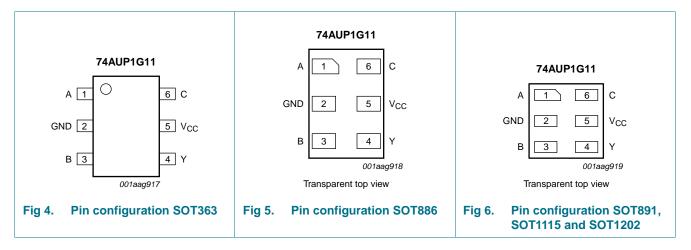
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

SymbolPinDescriptionA1data inputGND2ground (0 V)B3data inputY4data outputV _{CC} 5supply voltageC6data input	Table 3.	Pin description	
GND2ground (0 V)B3data inputY4data outputV _{CC} 5supply voltage	Symbol	Pin	Description
B3data inputY4data outputV _{CC} 5supply voltage	A	1	data input
Y4data outputV _{CC} 5supply voltage	GND	2	ground (0 V)
V _{CC} 5 supply voltage	В	3	data input
	Y	4	data output
C 6 data input	V _{CC}	5	supply voltage
	С	6	data input

7. Functional description

Table 4.Function table

Input		Output	
Α	В	C	Y
Н	Н	Н	Н
L	Х	Х	L
Х	L	Х	L
Х	Х	L	L

[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care.

Limiting values 8.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			-		-
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

Recommended operating conditions 9.

Table 6.	Recommended operating condition	ons			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_0 = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.31	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.31	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.5	μΑ
Δl _{CC}	additional supply current		<u>[1]</u> -	-	40	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF

Low-power 3-input AND gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = –	40 °C to +85 °C					
ViH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65\times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
√ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35\times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
√ _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I_{O} = 1.1 mA; V_{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I_{O} = 3.1 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
OFF	power-off leakage current	$V_{I} \text{ or } V_{O}$ = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μΑ
∆I _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μA
СС	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.9	μA
7l ^{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	50	μA

Table 7. Static characteristics ... continued

Low-power 3-input AND gate

	Parameter	; voltages are referenced to GND (groun Conditions	Min	Тур	Max	Unit
-	40 °C to +125 °C	Conditions		чур	WIAN	UII
∎amb – – V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	_	-	V
vін	nion-level input voltage	$\frac{V_{CC} = 0.8 \text{ V}}{V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}}$	$0.73 \times V_{CC}$ $0.70 \times V_{CC}$			V
		$\frac{V_{CC} = 0.9 \text{ V to } 1.93 \text{ V}}{V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}}$	1.6			V
		$\frac{V_{CC} = 2.5 \text{ V to } 2.7 \text{ V}}{V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}}$	2.0			v
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-		- 0.25 × V _{CC}	v
۷IL	LOw-level input voltage	$\frac{V_{CC} = 0.8 \text{ V}}{V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}}$	-		$0.23 \times V_{CC}$ $0.30 \times V_{CC}$	
		$\frac{V_{CC} = 0.9 \text{ V to } 1.93 \text{ V}}{V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}}$		-	0.30 × V _{CC}	V
		$\frac{v_{CC} = 2.3 \text{ V to } 2.7 \text{ V}}{V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}}$	-	-	0.9	V
1.	HIGH-level output voltage			-	0.9	v
V _{ОН}	Tiloti -level output voltage	$\frac{V_{I} = V_{IH} \text{ or } V_{IL}}{I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V to } 3.6 \ \text{V}}$	V _{CC} – 0.11			V
			$\frac{V_{CC} - 0.11}{0.6 \times V_{CC}}$	-	•	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.8 × V _{CC} 0.93	-	•	V V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.17	-	•	V V
		$I_0 = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		-	•	V V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$ $I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V V
			1.67	-	-	
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$\frac{V_{I} = V_{IH} \text{ or } V_{IL}}{V_{IL} = 20 \text{ m/s} V_{IL}}$			0.11	V
		$I_0 = 20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V to } 3.6 \ \text{V}$	-	-	0.11	
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
	in a standard and a summary t	$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μA
OFF	power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±0.75	μA
Al _{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
CC	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
∆I _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	75	μA

Table 7. Static characteristics ... continued

.... a 010

[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions			25 °C		-40	0 °C to +1	25 °C	Unit
			Ν	Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F									
t _{pd} propagation delay		A, B and C to Y; see <u>Figure 7</u>	[2]							
		$V_{CC} = 0.8 V$		-	18.9	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	:	3.0	5.6	9.5	2.8	9.9	10.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	4	2.3	3.9	5.9	2.2	6.5	6.8	ns
		V_{CC} = 1.65 V to 1.95 V		1.9	3.1	4.8	1.8	5.3	5.5	ns
		V_{CC} = 2.3 V to 2.7 V		1.6	2.5	3.6	1.4	4.0	4.2	ns
		V_{CC} = 3.0 V to 3.6 V		1.3	2.2	3.2	1.2	3.5	3.7	ns
C _L = 10 p	ρF									
pd	propagation delay	A, B and C to Y; see <u>Figure 7</u>	[2]							
		$V_{CC} = 0.8 V$		-	22.5	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	;	3.5	6.5	11.1	3.3	11.6	11.8	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	2	2.8	4.5	6.8	2.6	7.5	7.8	ns
		V _{CC} = 1.65 V to 1.95 V	2	2.4	3.7	5.6	2.1	6.2	6.4	ns
		V_{CC} = 2.3 V to 2.7 V		1.9	3.0	4.4	1.7	4.8	5.1	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.7	2.8	4.0	1.5	4.3	4.5	ns
C _L = 15 p	ρF									
pd	propagation delay	A, B and C to Y; see <u>Figure 7</u>	[2]							
		$V_{CC} = 0.8 V$		-	23.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3	3.9	7.3	12.5	3.6	13.3	13.4	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$:	3.2	5.1	7.6	2.9	8.5	8.8	ns
		V_{CC} = 1.65 V to 1.95 V	2	2.7	4.2	6.3	2.4	6.9	7.3	ns
		V_{CC} = 2.3 V to 2.7 V	2	2.3	3.5	5.0	2.0	5.5	5.8	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2	2.0	3.2	4.6	1.8	5.0	5.2	ns
C _L = 30 p	ρF									
pd	propagation delay	A, B and C to Y; see <u>Figure 7</u>	[2]							
		$V_{CC} = 0.8 V$		-	36.3	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	Ę	5.1	9.5	16.8	4.8	17.9	18.3	ns
		V_{CC} = 1.4 V to 1.6 V	4	4.2	6.7	10.0	3.8	11.3	11.8	ns
		V_{CC} = 1.65 V to 1.95 V	;	3.6	5.5	8.1	3.2	9.1	9.7	ns
		V_{CC} = 2.3 V to 2.7 V	;	3.0	4.6	6.6	2.8	7.2	7.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.7	4.3	6.1	2.5	6.6	6.9	ns

8 of 19

Symbol	Parameter	ameter Conditions 25 °C		tions			-4	0 °C to +1	25 °C	Unit
			ľ	Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF						1		
C _{PD} power dissipation capacitance		$f_i = 1 \text{ MHz};$ V _I = GND to V _{CC}	<u>[3]</u>							
		$V_{CC} = 0.8 V$		-	2.7	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	2.8	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V		-	2.9	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V		-	3.1	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	3.5	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.1	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

-----010.6

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

12. Waveforms

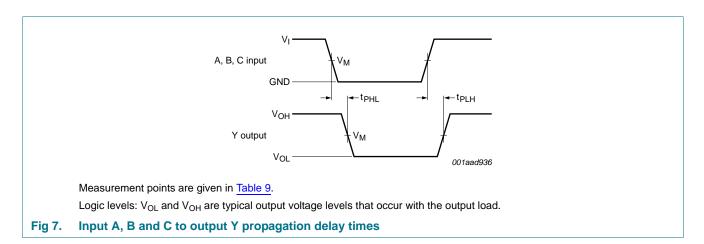


Table 9. **Measurement points**

Supply voltage	Output	Input					
V _{CC}	V _M	V _M	VI	$t_r = t_f$			
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{CC}	≤ 3.0 ns			

74AUP1G11 **Product data sheet**

Low-power 3-input AND gate

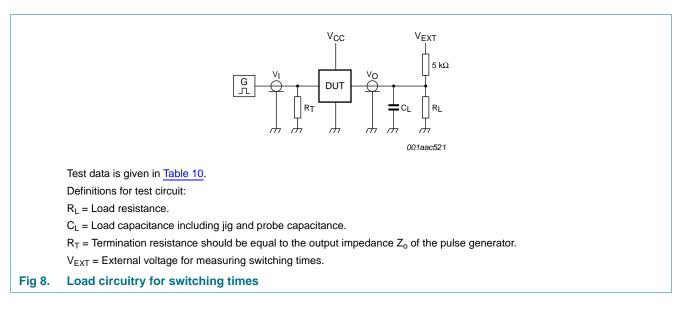


Table 10.Test data

Supply voltage	Load		V _{EXT}		
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

Low-power 3-input AND gate

13. Package outline

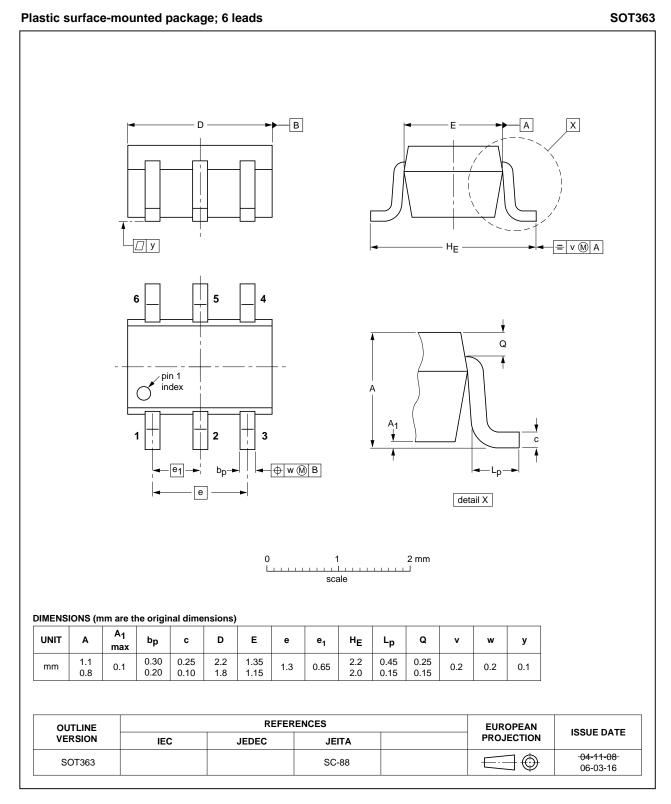


Fig 9. Package outline SOT363 (SC-88)

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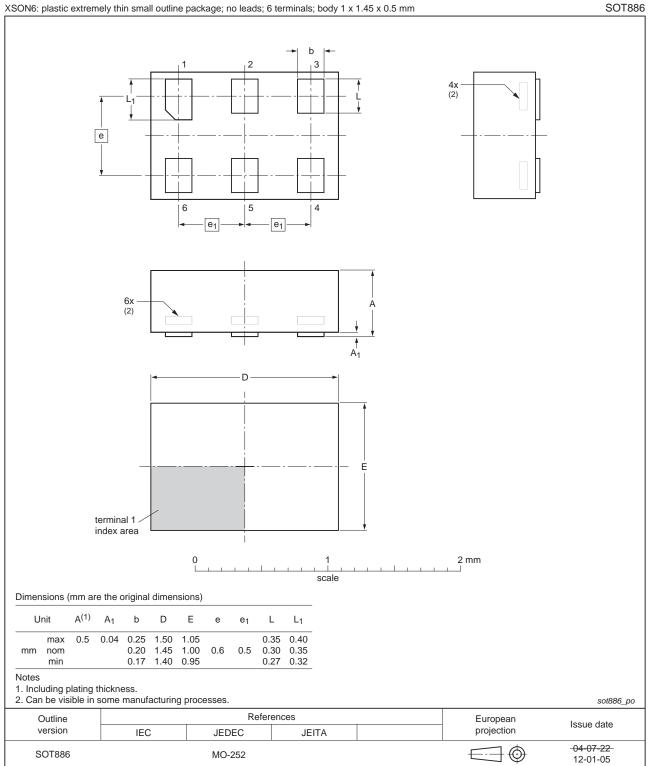


Fig 10. Package outline SOT886 (XSON6)

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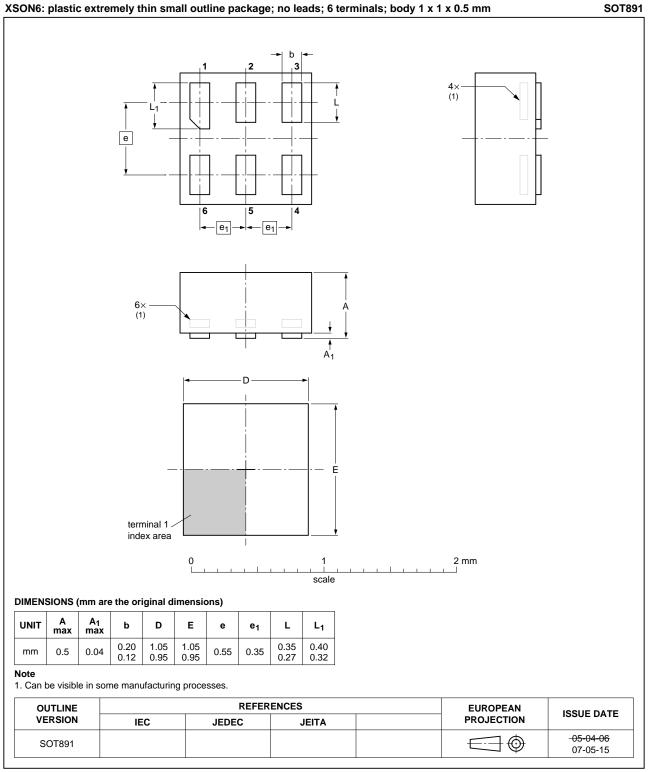
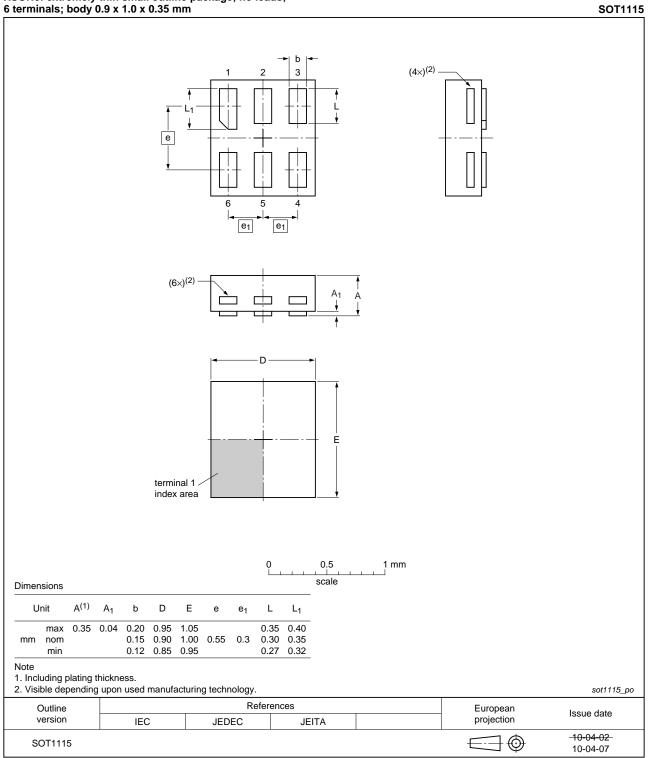


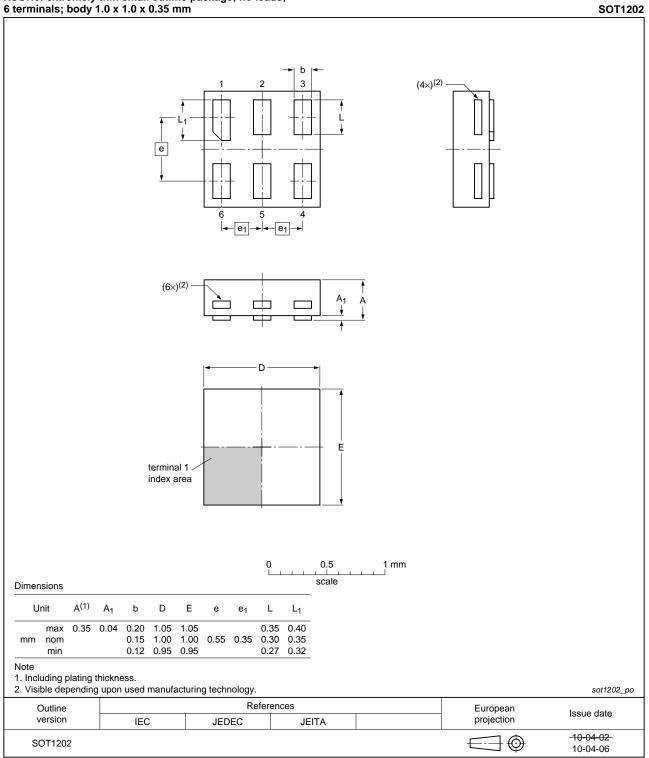
Fig 11. Package outline SOT891 (XSON6)

74AUP1G11 **Product data sheet**



XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 12. Package outline SOT1115 (XSON6)



XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1202 (XSON6)

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14. Abbreviations

Table 11. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G11 v.4	20120803	Product data sheet	-	74AUP1G11 v.3
Modifications:	 Package ou 	tline drawing of SOT886 (F	igure 10) modified.	
74AUP1G11 v.3	20111124	Product data sheet	-	74AUP1G11 v.2
Modifications:	 Legal pages 	s updated.		
74AUP1G11 v.2	20101020	Product data sheet	-	74AUP1G11 v.1
74AUP1G11 v.1	20070904	Product data sheet	-	-

16. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Low-power 3-input AND gate

18. Contents

1	General description 1
2	Features and benefits 1
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning 3
6.2	Pin description 3
7	Functional description 3
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 5
11	Dynamic characteristics 8
12	Waveforms
13	Package outline 11
14	Abbreviations 16
15	Revision history 16
16	Legal information
16.1	Data sheet status 17
16.2	Definitions 17
16.3	Disclaimers
16.4	Trademarks
17	Contact information 18
18	Contents 19

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